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# Amorphous Semiconductors for Microelectronics

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# AMORPHOUS SEMICONDUCTORS FOR MICROELECTRONICS

Volume 617

## Contents

Conference Committee .....	iv
Introduction .....	v
<b>SESSION 1. THIN-FILM TRANSISTORS.</b> .....	1
617-01 <b>Amorphous semiconductors for microelectronics</b> , S. R. Ovshinsky, Energy Conversion Devices, Inc. ....	2
617-02 <b>The demands on the a-Si FET as a pixel switch for liquid crystal displays</b> , W. W. Piper, J. E. Bigelow, D. E. Castleberry, G. E. Possin, General Electric Co. ....	10
617-03 <b>Progress in two and three terminal amorphous silicon switching devices for matrix addressed LCDs</b> , Z. Yaniv, V. Cannella, A. Lien, J. McGill, W. den Boer, Ovonic Display Systems, Inc. ....	16
617-04 <b>High-barrier rectifying junctions with amorphous silicon alloy electrodes and their application to FET's for LSI's</b> , K. Murase, M. Suzuki, NTT Electrical Communications Labs. (Japan). ....	25
617-05 <b>Amorphous silicon alloy thin film transistor operation with high field effect mobility</b> , M. Shur, C. Hyun, Univ. of Minnesota; M. Hack, W. Czubatyj, Energy Conservation Devices, Inc. ....	33
<b>SESSION. 2. PHYSICS OF AMORPHOUS-SILICON DEVICES.</b> .....	43
617-06 <b>Hydrogenated amorphous silicon and microcrystalline silicon for the emitter of silicon bipolar transistors</b> , M. Ghannam, J. Nijs, R. De Keersmaecker, R. Mertens, IMEC (Belgium) ....	44
617-07 <b>Bulk limitation effects in amorphous silicon alloy diodes</b> , V. Cannella, J. McGill, Z. Yaniv, Ovonic Display Systems, Inc.; M. Silver, MIT. ....	51
617-08 <b>Contact resistance measurement technique for amorphous semiconductors</b> , H. Schade, Z. E. Smith, RCA Labs. ....	56
617-09 <b>In situ studies of the bulk and interface structure of a-Si:H</b> , R. W. Collins, The Standard Oil Co. Research Ctr. ...	62
617-10 <b>Picosecond decay of photoinduced absorption in hydrogenated amorphous silicon</b> , D. M. Roberts, T. L. Gustafson, The Standard Oil Co. (Ohio) ....	71
<b>SESSION 3. AMORPHOUS SILICON PHOTORECEPTORS</b> .....	81
617-11 <b>Photoconductors in electrophotography</b> , D. M. Pai, A. R. Melnyk, Xerox Corp. ....	82
617-12 <b>Amorphous silicon alloy photoreceptors</b> , S. J. Hudgens, Energy Conversion Devices, Inc. ....	95
617-13 <b>a-Si photoreceptors at the threshold of industrial application</b> , W. Senske, N. Marschall, AEG-Forschungsinstitut (West Germany) .....	102
617-14 <b>Multilayered amorphous silicon photoreceptors and their application to optical printers</b> , H. Kakinuma, S. Nishikawa, T. Watanabe, K. Nihei, Oki Electric Industry Co., Ltd. (Japan). ....	109
617-15 <b>Amorphous silicon image pickup tubes</b> , S. Ishioka, C. Kusano, Y. Takasaki, Y. Shimomoto, T. Hirai, Hitachi Ltd. (Japan). ....	115
<b>SESSION 4. IMAGE SENSORS AND POWER SENSORS.</b> .....	119
617-16 <b>a-Si:H image sensor: some aspects of physics and performance</b> , K. Kempter, Siemens A.G. (West Germany) ..	120
617-17 <b>Amorphous Si:H contact linear image sensor</b> , S. Kaneko, F. Okumura, M. Sakamoto, H. Uchida, Y. Kajiwara, NEC Corp. (Japan) .....	127
617-18 <b>Recent development in amorphous silicon image sensor</b> , T. Ozawa, M. Takenouchi, Fuji Xerox Co., Ltd. (Japan). ....	133
617-19 <b><math>\mu</math>c-Si:H:F thermopile power sensors</b> , S. Kodato, Anritsu Corp. (Japan) .....	140
Addendum .....	147
Author Index .....	148